

Hiroshi Hiroshima

List of Publications by Year in descending order

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136
papers

2,169
citations

236925

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137
all docs

137
docs citations

137
times ranked

849
citing authors

#	ARTICLE	IF	CITATIONS
1	Development of simple high-resolution embedded printing for transparent metal grid conductors. Applied Physics Letters, 2017, 111, .	3.3	10
2	12-inch X-ray optics based on MEMS process. Microsystem Technologies, 2017, 23, 2815-2821.	2.0	4
3	Bubble-free patterning with low line edge roughness by ultraviolet nanoimprinting using trans-1,3,3,3-tetrafluoropropene condensable gas. Applied Physics Letters, 2016, 109, .	3.3	10
4	Ultraviolet Nanoimprint Lithography in the Mixture of Condensable Gases with Different Vapor Pressures. Journal of Photopolymer Science and Technology = [Fotoporima Konwakai Shi], 2016, 29, 181-187.	0.3	4
5	Fine and high-aspect-ratio screen printing combined with an imprinting technique. Journal of Micromechanics and Microengineering, 2016, 26, 035005.	2.6	6
6	Bubble-free high-speed UV nanoimprint lithography using condensable gas with very low global warming potential. Japanese Journal of Applied Physics, 2016, 55, 076502.	1.5	6
7	Selective Cu Patterning on Polyimide Using UV Surface Treatment and Electroless Plating. Journal of Photopolymer Science and Technology = [Fotoporima Konwakai Shi], 2015, 28, 157-161.	0.3	3
8	Innovative UV nanoimprint lithography using a condensable alternative chlorofluorocarbon atmosphere. Microelectronic Engineering, 2015, 133, 134-155.	2.4	45
9	Resin filling of UV-cured nanoimprints using pentafluoropropane to fabricate large patterns with a thin residual layer. Microelectronic Engineering, 2015, 136, 81-84.	2.4	1
10	Atomic step patterning on quartz glass via thermal nanoimprinting. Japanese Journal of Applied Physics, 2015, 54, 098001.	1.5	4
11	Nano-patterning on soluble block copolymer polyimide by nanoimprint. Japanese Journal of Applied Physics, 2015, 54, 088002.	1.5	4
12	Simple fabrication process for UV nanoimprint mold with embedded metal alignment marks for in-liquid alignment. Japanese Journal of Applied Physics, 2014, 53, 06JK01.	1.5	3
13	Immersion effect of fluoride liquid into cavities of negative mold in thermal imprint. Microsystem Technologies, 2013, 19, 599-608.	2.0	1
14	Fabrication of sub 20-nm wide grooves in a quartz mold by space narrowing dry etching. Microelectronic Engineering, 2013, 110, 432-435.	2.4	4
15	Study of Demolding Characteristics in Step-and-Repeat Ultraviolet Nanoimprinting. Japanese Journal of Applied Physics, 2013, 52, 06CJ04.	1.5	3
16	Improved Performances of All-Polyimide Fluidic Devices Using Thermal Nanoimprinting. Applied Mechanics and Materials, 2013, 300-301, 1360-1363.	0.2	0
17	Simplified Cu/Polyimide Damascene Approach Based on Imprint Process of Soluble Block Copolymer Polyimide. Japanese Journal of Applied Physics, 2013, 52, 10MD03.	1.5	1
18	Control of Resin Filling and Pattern Quality of Ultraviolet Nanoimprint Lithography in Pentafluoropropane and Helium Ambient. Japanese Journal of Applied Physics, 2013, 52, 06CJ07.	1.5	7

#	ARTICLE	IF	CITATIONS
19	Uniform Residual Layer Creation in Ultraviolet Nanoimprint Using Spin Coat Films for Sub-100-nm Patterns with Various Pattern Densities. Japanese Journal of Applied Physics, 2013, 52, 06GJ06.	1.5	5
20	Uniform Thermal Nanoimprinting at Low Pressure by Improved Heat Transfer Using Hydrofluoroethers. Japanese Journal of Applied Physics, 2013, 52, 06GJ02.	1.5	2
21	A Study on Surface Modification of Soluble Block Copolymer Polyimide by UV Irradiation and Its Application to Electroless Plating. Journal of Photopolymer Science and Technology = [Fotoporima Konwakai Shi], 2013, 26, 297-302.	0.3	2
22	Simulation of Resist Filling Properties under Condensable Gas Ambient in Ultraviolet Nanoimprint Lithography. Japanese Journal of Applied Physics, 2012, 51, 06FJ07.	1.5	5
23	Effective Linewidth Measurement of 45-nm-Half-Pitch Ultraviolet Nanoimprint Lithography Patterns by Scanning Electron Microscope Inspection and Extremely Shallow Si Etching. Japanese Journal of Applied Physics, 2012, 51, 06FJ09.	1.5	1
24	Throughput of Ultraviolet Nanoimprint in Pentafluoropropane Using Spin Coat Films under Thin Residual Layer Conditions. Japanese Journal of Applied Physics, 2012, 51, 06FJ10.	1.5	9
25	In-situ Evaluation of Air/Oxygen Percentage Variation by Introducing 1,1,1,3,3-Pentafluoropropane in Ultraviolet Nanoimprint Lithography. Japanese Journal of Applied Physics, 2012, 51, 118002.	1.5	4
26	Step and Repeat Ultraviolet Nanoimprinting under Pentafluoropropane Gas Ambient. Japanese Journal of Applied Physics, 2012, 51, 06FJ08.	1.5	4
27	Adhesion and frictional force measurements employing scanning probe microscopy in a pentafluoropropane gas atmosphere. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2012, 30, 011601.	1.2	2
28	Transfer of Relatively Large Microstructures on Polyimide Films using Thermal Nanoimprinting. Journal of Photopolymer Science and Technology = [Fotoporima Konwakai Shi], 2012, 25, 255-260.	0.3	9
29	Immersion nanoimprint lithography using perfluoroalkyl liquid. Microelectronic Engineering, 2012, 97, 43-47.	2.4	1
30	Real-time full-area monitoring of the filling process in molds for UV nanoimprint lithography using dark field illumination. Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics, 2012, 30, 06FB13.	1.2	3
31	Morphological Changes in Ultraviolet-Nanoimprinted Resin Patterns Caused by Ultraviolet-Curable Resins Absorbing Pentafluoropropane. Japanese Journal of Applied Physics, 2012, 51, 06FJ05.	1.5	9
32	Effect of Dropping Hydrofluoroether in Thermal Nanoimprint on Polycarbonate. Japanese Journal of Applied Physics, 2011, 50, 06GK05.	1.5	2
33	Fabrication Processes for Capacity-Equalized Mold with Fine Patterns. Japanese Journal of Applied Physics, 2011, 50, 06GK04.	1.5	1
34	High Temporal Resolution Measurements of Shrinkage Characteristics of UV Nanoimprint Resin. Journal of Photopolymer Science and Technology = [Fotoporima Konwakai Shi], 2011, 24, 95-100.	0.3	4
35	Cylindrical projection lithography for microcoil structures. Microelectronic Engineering, 2011, 88, 2625-2628.	2.4	20
36	Fluorescent Microscopy Proving Resin Adhesion to a Fluorinated Mold Surface Suppressed by Pentafluoropropane in Step-and-Repeat Ultraviolet Nanoimprinting. Japanese Journal of Applied Physics, 2011, 50, 06GK02.	1.5	23

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37	Effects of Granularity of Complementary Patterns in a Capacity-Equalized Mold Used for UV Nanoimprint Lithography. Japanese Journal of Applied Physics, 2011, 50, 06GK08.	1.5	2
38	Study on Quartz Multitier Mold Fabrication Using Gray Scale Laser Beam Lithography. Japanese Journal of Applied Physics, 2011, 50, 06GK03.	1.5	1
39	Evaluation of the curing process of UV resins in a 1,1,1,3,3-pentafluoropropane gas environment by photo differential scanning calorimetry and Fourier transform infrared spectroscopy. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2011, 29, 06FC05.	1.2	0
40	Anisotropic filling phenomenon of cavities in UV nanoimprint lithography. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2011, 29, 06FC19.	1.2	1
41	Characterization of pentafluoropropane dissolved UV-nanoimprint resin. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2011, 29, 06FC18.	1.2	1
42	Study on Change in UV Nanoimprint Pattern by Altering Shrinkage of UV Curable Resin. Japanese Journal of Applied Physics, 2011, 50, 06GK09.	1.5	13
43	Viscosity of a Thin Film of UV Curable Resin in Pentafluoropropane. Journal of Photopolymer Science and Technology = [Fotoporima Konwakai Shi], 2010, 23, 45-50.	0.3	24
44	A Dynamic System to evaluate the UV Shrinkage Characteristics of UV Photopolymers used for Nanoimprint. Journal of Photopolymer Science and Technology = [Fotoporima Konwakai Shi], 2010, 23, 33-38.	0.3	17
45	Viscosity Measurement of Spin-coated UV Nanoimprint Resin. Journal of Photopolymer Science and Technology = [Fotoporima Konwakai Shi], 2010, 23, 19-24.	0.3	2
46	3D UV-microreplication using cylindrical PDMS mold. Microsystem Technologies, 2010, 16, 1399-1411.	2.0	7
47	Effects of Environmental Gas in UV Nanoimprint on the Characteristics of UV-Curable Resin. Japanese Journal of Applied Physics, 2010, 49, 06GL04.	1.5	32
48	45 nm hp line/space patterning into a thin spin coat film by UV nanoimprint based on condensation. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2010, 28, C6M12-C6M16.	1.2	23
49	Evaluation of Viscosity Characteristics of Spin-Coated UV Nanoimprint Resin. Japanese Journal of Applied Physics, 2010, 49, 06GL10.	1.5	2
50	UV Nanoimprint in Pentafluoropropane at a Minimal Imprint Pressure. Japanese Journal of Applied Physics, 2010, 49, 06GL01.	1.5	15
51	Size Dependence of Quick Cavity Filling Behavior in Ultraviolet Nanoimprint Lithography Using Pentafluoropropane Gas. Japanese Journal of Applied Physics, 2010, 49, 06GL06.	1.5	26
52	Residual layer uniformity using complementary patterns to compensate for pattern density variation in UV nanoimprint lithography. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2010, 28, C6M125-C6M129.	1.2	9
53	Release force reduction in UV nanoimprint by mold orientation control and by gas environment. Journal of Vacuum Science & Technology B, 2009, 27, 2862-2865.	1.3	35
54	Numerical study on bubble trapping in UV nanoimprint lithography. Journal of Vacuum Science & Technology B, 2009, 27, 2866.	1.3	36

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55	Homogeneity of Residual Layer thickness in UV Nanoimprint Lithography. Japanese Journal of Applied Physics, 2009, 48, 06FH18.	1.5	10
56	3D replication using PDMS mold for microcoil. Microelectronic Engineering, 2009, 86, 920-924.	2.4	13
57	Nanoimprint with thin and uniform residual layer for various pattern densities. Microelectronic Engineering, 2009, 86, 611-614.	2.4	28
58	Numerical study on bubble trapping in UV-nanoimprint lithography. Microelectronic Engineering, 2009, 86, 684-687.	2.4	26
59	Simulation Study on Bubble Trapping in UV Nanoimprint Lithography. Journal of Photopolymer Science and Technology = [Fotoporima Konwakai Shi], 2009, 22, 171-174.	0.3	19
60	Evaluation of Viscosity Characteristics of UV Nanoimprint Resin in a Thin Film. Journal of Photopolymer Science and Technology = [Fotoporima Konwakai Shi], 2009, 22, 155-160.	0.3	7
61	Numerical simulation of time and temperature dependent polymer deformation in thermal imprint process. , 2008, , .		0
62	Fabrication of Ultrasmooth Mirrors by UV-Nanoimprint. Japanese Journal of Applied Physics, 2008, 47, 5156-5159.	1.5	2
63	Fabrication of Capacity-Equalized Mold for Homogenizing Residual Layer Thickness in Imprint Lithography. Japanese Journal of Applied Physics, 2008, 47, 8098.	1.5	20
64	Quick Cavity Filling in UV Nanoimprint Using Pentafluoropropane. Japanese Journal of Applied Physics, 2008, 47, 5151-5155.	1.5	40
65	Quick Cavity Filling in UV-Nanoimprint Using Pentafluoropropane. , 2007, , .		1
66	Fabrication of ultra smooth mirrors by UV-nanoimprint. , 2007, , .		0
67	UV-nanoimprint with the assistance of gas condensation at atmospheric environmental pressure. Journal of Vacuum Science & Technology B, 2007, 25, 2333-2336.	1.3	56
68	Control of Bubble Defects in UV Nanoimprint. Japanese Journal of Applied Physics, 2007, 46, 6391.	1.5	131
69	Evaluation of UV-Nanoimprinted Surface Roughness Using Si Mold with Atomically Flat Terraces. Japanese Journal of Applied Physics, 2007, 46, L1083-L1085.	1.5	5
70	Photo-Nanoimprinting Using Sample-on-Flexible-Thruster Stage. Japanese Journal of Applied Physics, 2006, 45, 5602-5606.	1.5	37
71	Photo-nanoimprint lithography combined with thermal treatment to improve resist pattern line-edge roughness. Nanotechnology, 2006, 17, 2219-2222.	2.6	7
72	Fidelity of Photo-nanoimprint. Journal of Photopolymer Science and Technology = [Fotoporima Konwakai Shi], 2005, 18, 537-542.	0.3	2

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73	Line Width Reproducibility of Photo-Nanoimprints. Japanese Journal of Applied Physics, 2005, 44, 5622-5626.	1.5	5
74	Fabrication of Low Line Edge Roughness Mold by Spin On Glass (SOG) Replica Method. Japanese Journal of Applied Physics, 2005, 44, 5617-5621.	1.5	7
75	Reducing Photocurable Polymer Pattern Shrinkage and Roughness during Dry Etching in Photo-Nanoimprint Lithography. Japanese Journal of Applied Physics, 2004, 43, 4022-4026.	1.5	8
76	Fabrication of Low Line Edge Roughness Mold for Photo-Nanoimprint. Japanese Journal of Applied Physics, 2004, 43, 4045-4049.	1.5	14
77	Step-and-Repeat Photo-Nanoimprint System Using Active Orientation Head. Japanese Journal of Applied Physics, 2004, 43, 4012-4016.	1.5	14
78	Fabrication of trilayer resist using photocuring-imprint lithography. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2003, 21, 3144.	1.6	3
79	Elimination of Pattern Defects of Nanoimprint under Atmospheric Conditions. Japanese Journal of Applied Physics, 2003, 42, 3849-3853.	1.5	63
80	Evaluation of Line Edge Roughness in Nanoimprint Lithography Using Photocurable Polymer. Japanese Journal of Applied Physics, 2003, 42, 3871-3873.	1.5	31
81	Measurement of Adhesive Force Between Mold and Photocurable Resin in Imprint Technology. Japanese Journal of Applied Physics, 2002, 41, 4194-4197.	1.5	80
82	Diamond nanoimprint lithography. Nanotechnology, 2002, 13, 592-596.	2.6	64
83	Room Temperature Nanoimprint Technology Using Hydrogen Silsequioxane (HSQ). Japanese Journal of Applied Physics, 2002, 41, 4198-4202.	1.5	56
84	Close Observation of the Geometrical Features of an Ultranarrow Silicon Nanowire Device. Japanese Journal of Applied Physics, 2002, 41, 4419-4422.	1.5	2
85	Improvement of Imprinted Pattern Uniformity Using Sapphire Mold. Japanese Journal of Applied Physics, 2002, 41, 4182-4185.	1.5	15
86	Uniformity in Patterns Imprinted Using Photo-Curable Liquid Polymer. Japanese Journal of Applied Physics, 2002, 41, 4173-4177.	1.5	49
87	Room temperature replication in spin on glass by nanoimprint technology. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2001, 19, 2801.	1.6	86
88	Single electron memory characteristic of silicon nanodot nanowire transistor. Electronics Letters, 2000, 36, 1322.	1.0	11
89	Properties of Si nanowire devices fabricated by using an inorganic EB resist process. Superlattices and Microstructures, 2000, 28, 453-460.	3.1	7
90	Nanolithography by electron beam resist-trimming technique. Superlattices and Microstructures, 2000, 28, 469-475.	3.1	1

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91	Beam-assisted-etching technique for fabrication of single crystal diamond field emitter tip. <i>Microelectronic Engineering</i> , 2000, 53, 415-418.	2.4	11
92	Highly suppressed short-channel effects in ultrathin SOI n-MOSFETs. <i>IEEE Transactions on Electron Devices</i> , 2000, 47, 354-359.	3.0	103
93	Fabrication technology of a Si nanowire memory transistor using an inorganic electron beam resist process. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2000, 18, 2640.	1.6	13
94	Preparation of Diamond Mold Using Electron Beam Lithography for Application to Nanoimprint Lithography. <i>Japanese Journal of Applied Physics</i> , 2000, 39, 7070-7074.	1.5	31
95	Imprint Characteristics by Photo-Induced Solidification of Liquid Polymer. <i>Japanese Journal of Applied Physics</i> , 2000, 39, 7075-7079.	1.5	126
96	Conditions for Fabrication of Highly Conductive Wires by Electron-Beam-Induced Deposition. <i>Japanese Journal of Applied Physics</i> , 1999, 38, 7135-7139.	1.5	37
97	Fabrication of 40-150 nm Gate Length Ultrathin n-MOSFETs Using Epitaxial Layer Transfer SOI Wafers. <i>Japanese Journal of Applied Physics</i> , 1999, 38, 2492-2495.	1.5	3
98	Fabrication and characterization of a nanogap edge emitter with a silicon-on-insulator wafer. <i>Applied Surface Science</i> , 1999, 146, 203-208.	6.1	19
99	Field emission from electron-beam-irradiated bulk diamond. <i>Applied Surface Science</i> , 1999, 146, 299-304.	6.1	2
100	Fabrication of a Nanometer-Scale Si-Wire by Micromachining of a Silicon-on-Insulator Substrate. <i>Japanese Journal of Applied Physics</i> , 1998, 37, 7182-7185.	1.5	19
101	Fabrication of conductive wires by electron-beam-induced deposition. <i>Nanotechnology</i> , 1998, 9, 108-112.	2.6	23
102	Printing Sub-100 Nanometer Features Near-field Photolithography. <i>Japanese Journal of Applied Physics</i> , 1998, 37, 6739-6744.	1.5	9
103	Miniature tunnel junction by electron-beam-induced deposition. <i>Nanotechnology</i> , 1998, 9, 104-107.	2.6	13
104	The use of a Si-based resist system and Ti electrode for the fabrication of sub-10 nm metal-insulator-metal tunnel junctions. <i>Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films</i> , 1998, 16, 1430-1434.	2.1	12
105	Development of SiO ₂ /c-Si bilayer e-beam resist process and its application for 10-nm-scale MIM junctions. , 1998, , .		0
106	High Growth Rate for Slow Scanning in Electron-Beam-Induced Deposition. <i>Japanese Journal of Applied Physics</i> , 1997, 36, 7686-7690.	1.5	20
107	Electron Beam Assisted Chemical Etching of Single-Crystal Diamond Substrates with Hydrogen Gas. <i>Japanese Journal of Applied Physics</i> , 1997, 36, 7691-7695.	1.5	15
108	Electron beam dot lithography for nanometer-scale tunnel junctions using a double-layered inorganic resist. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 1997, 15, 1406.	1.6	7

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109	Diameter dependence of current-voltage characteristics of ultrasmall area AlSb-InAs resonant tunneling diodes with diameters down to 20 nm. Applied Physics Letters, 1997, 70, 2025-2027.	3.3	16
110	Lateral tunnel junction produced by electron-beam-induced deposition. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1997, 15, 2809.	1.6	14
111	Fabrication and properties of dot array using electron-beam-induced deposition. Microelectronic Engineering, 1997, 35, 273-276.	2.4	34
112	Electron beam nano-fabrication by inorganic resist for MIM tunnel junction. Microelectronic Engineering, 1996, 30, 411-414.	2.4	4
113	SiO ₂ /poly-Si electron beam resist process for nanofabrication. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 1996, 14, 1850-1854.	2.1	5
114	SiO ₂ /c-Si Bilayer Electron-Beam Resist Process for Nano-Fabrication. Japanese Journal of Applied Physics, 1996, 35, 6673-6678.	1.5	8
115	Fabrication of High-Resolution Fresnel Zone Plates by a Single Layer Resist Process. Japanese Journal of Applied Physics, 1996, 35, 6447-6451.	1.5	1
116	Electron beam writing and direct processing system for nanolithography. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 1995, 363, 73-78.	1.6	7
117	Nanobeam process system: An ultrahigh vacuum electron beam lithography system with 3 nm probe size. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1995, 13, 2514.	1.6	23
118	SiO ₂ /Poly-Si Multilayered Electron Beam Resist Process for Fabrication of Ultrasmall Tunnel Junctions. Japanese Journal of Applied Physics, 1995, 34, 6961-6965.	1.5	9
119	Characteristics of SiO ₂ as a High-Resolution Electron Beam Resist. Japanese Journal of Applied Physics, 1993, 32, 6153-6157.	1.5	25
120	A Focused He ⁺ Ion Beam with a High Angular Current Density. Japanese Journal of Applied Physics, 1992, 31, 4492-4495.	1.5	2
121	Fine pattern definition with atomic intermixing induced by focused ion beam and its application to x-ray mask fabrication. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1991, 9, 295.	1.6	0
122	Focused Ga ion beam etching characteristics of GaAs with Cl ₂ . Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1991, 9, 2656.	1.6	18
123	Focused Ga Ion Beam Etching of Si in Chlorine Gas. Japanese Journal of Applied Physics, 1990, 29, 2288-2291.	1.5	18
124	Miniature Hall sensor fabricated with maskless ion implantation. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1988, 6, 1010.	1.6	13
125	1/f noise in a quarter-micron GaAs Hall device made by focused ion beam implantation. Journal of Applied Physics, 1987, 62, 4301-4303.	2.5	9
126	Maskless etching of a nanometer structure by focused ion beams. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 1983, 1, 985.	1.6	59

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127	Measurement of virtual crossover in liquid gallium ion source. Applied Physics Letters, 1983, 42, 908-910.	3.3	48
128	Fabrication technology of Si nanodot nanowire memory transistors using an inorganic EB resist process. , 0, , .		1
129	Imprinting characteristics by photo-induced solidification of liquid polymer. , 0, , .		0
130	Compact imprint system using driving power of stepping motor. , 0, , .		1
131	Diamond mold for nanoimprint lithography. , 0, , .		0
132	Improvement of imprinted pattern uniformity using sapphire mold. , 0, , .		0
133	Measurement of adhesive force between mold and photo-curable resin in imprint technology. , 0, , .		0
134	Uniformity in patterns imprinted using photo-curable liquid polymer. , 0, , .		0
135	Electrical and geometrical properties of a Si quantum nanowire device fabricated by an inorganic EB resist process. , 0, , .		0
136	Room temperature nanoimprint technology. , 0, , .		0